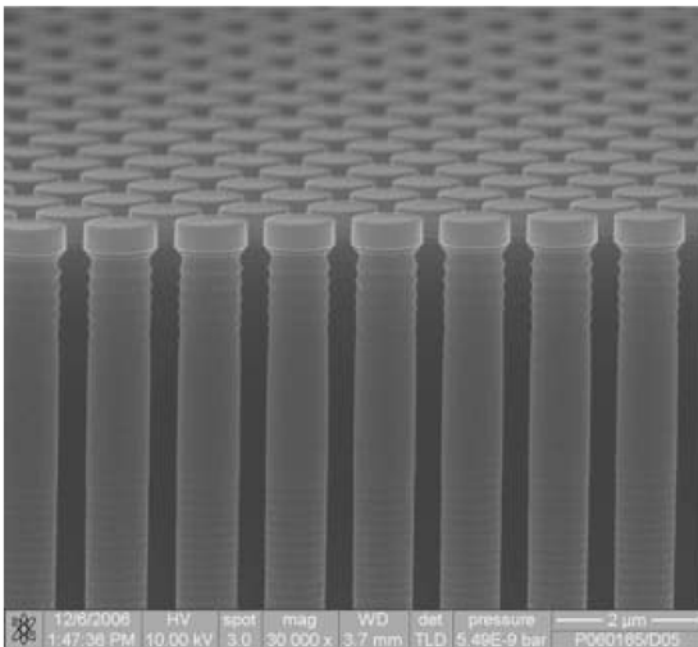
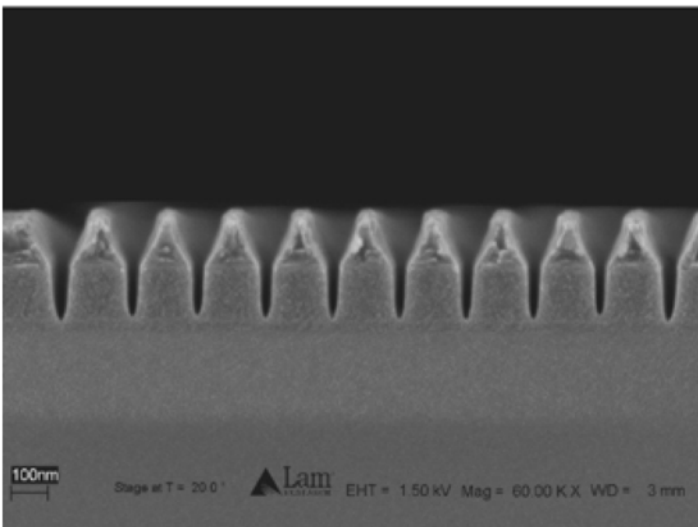


**32nm half pitch poly Si gates
plasma etched using a double patterning
lithography technique.**



**Deep Si etching for a liquid
separation device.**



**Etch of 30-nm wide trenches in a
k=3.0 low-k material, using a next-
generation patterning technique.**